

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	5	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	25	mA
				50	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	50	mA
				60	
I_H	$I_T=200mA$		MAX.	40	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	300	V/ μs
$(dV/dt)_c$	$(dI/dt)_c=2.7A/ms$, $T_j=125$		MIN.	5	V/ μs
t_{on}	$I_G=80mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX.)	Unit
V_{TM}	$I_{TM}=8.5A$ t		

ORDERING INFORMATION

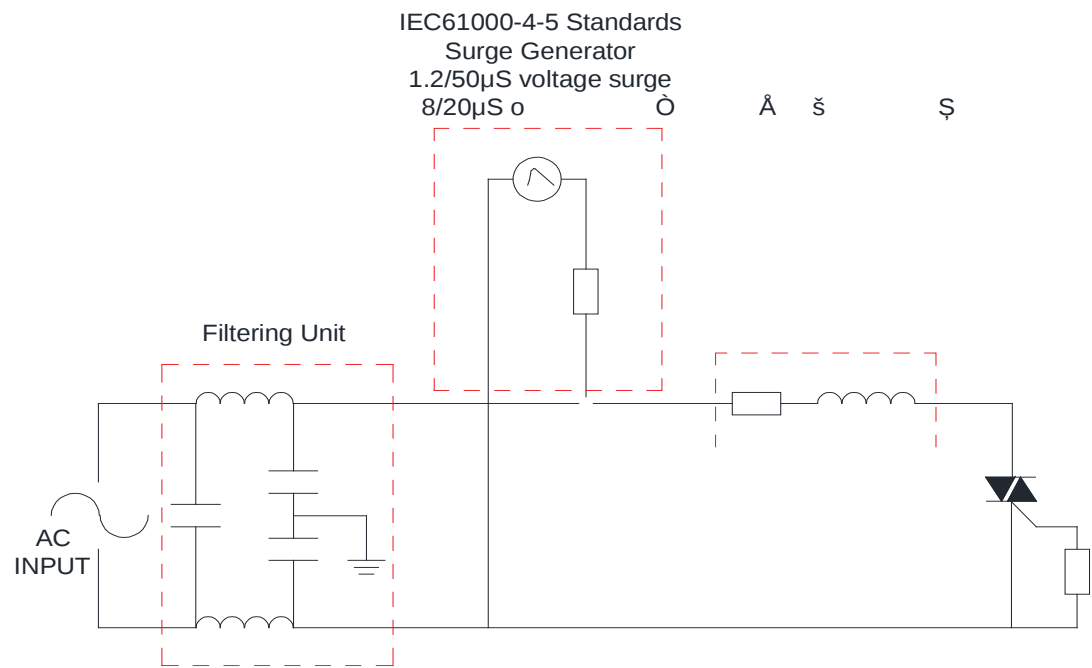
J	ST	06	C	-800	C
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:6A$	$C:TO-220C$	$800:V_{DRM}/V_{RRM} \geq 800V$	$C:I_{GT1-3} \leq 25mA \ I_{GT4} \leq 50mA$

MARKING



FIG.1: Max 0437 (c)mu c 0 d437 (c)scccp 0er2.45cc (c) RTJ 0 (cM)]TJTT31.2 (4T3 1 Tf -0.006 Tw J 0102 W .4

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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